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Renesas Electronics website: <http://www.renesas.com>

April 1st, 2010
Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (<http://www.renesas.com>)

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MOS FIELD EFFECT TRANSISTOR

84N06CLD, NP84N06DLD, NP84N06ELD

SWITCHING

N-CHANNEL POWER MOS FET

INDUSTRIAL USE

DESCRIPTION

This product is N-Channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Channel temperature 175 degree rated
- Super low on-state resistance
 $R_{DS(on)1} = 6.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 42 \text{ A)}$
 $R_{DS(on)2} = 9.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = 5 \text{ V, } I_D = 35 \text{ A)}$
- Built-in gate protection diode

ORDERING INFORMATION

PART NUMBER	PACKAGE
NP84N06CLD	TO-220AB
NP84N06DLD	TO-262
NP84N06ELD	TO-263

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V _{GS} = 0)	V _{DSS}	60	V
Gate to Source Voltage (V _{DS} = 0)	V _{GSS}	±20	V
Drain Current (DC) ^{Note1}	I _{D(DC)}	±84	A
Drain Current (Pulse) ^{Note2}	I _{D(pulse)}	±280	A
Total Power Dissipation (T _A = 25°C)	P _{T1}	1.8	W
Total Power Dissipation (T _C = 25°C)	P _{T2}	185	W
Channel Temperature	T _{ch}	175	°C
Storage Temperature	T _{stg}	-55 to +175	°C
Single Avalanche Current ^{Note3}	I _{AS}	Figure4	A
Single Avalanche Energy ^{Note3}	E _{AS}	Figure4	mJ
Repetitive Avalanche Current ^{Note4}	I _{AR}	70	A
Repetitive Avalanche Energy ^{Note4}	E _{AR}	490	mJ

- Notes**
1. Package Limit = ± 75 A
 2. PW ≤ 10 μs, Duty cycle ≤ 1 %
 3. Starting T_{ch} = 25°C, R_G = 25 Ω, V_{GS} = 20 V → 0 V
 4. T_{ch} ≤ 175°C, R_G = 25 Ω, V_{GS} = 20 V → 0 V, Duty cycle ≤ 3%

THERMAL RESISTANCE

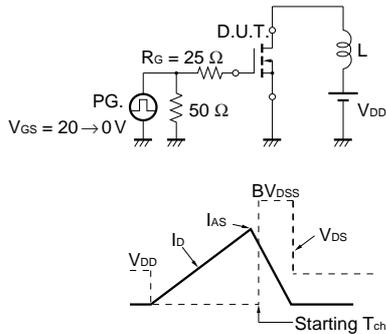
Channel to Case	R _{th(ch-C)}	0.81	°C/W
Channel to Ambient	R _{th(ch-A)}	83.3	°C/W

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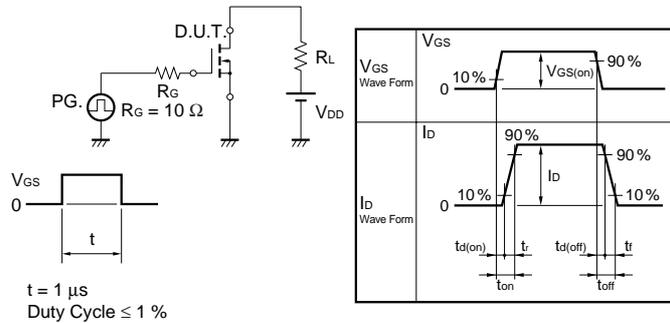
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	$R_{DS(on)1}$	$V_{GS} = 10\text{ V}, I_D = 42\text{ A}$		5.5	6.5	mΩ
	$R_{DS(on)2}$	$V_{GS} = 5\text{ V}, I_D = 35\text{ A}$		6.4	9.5	mΩ
	$R_{DS(on)3}$	$V_{GS} = 4\text{ V}, I_D = 35\text{ A}$		7.0	10.5	mΩ
Gate to Source Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.0	1.5	2.0	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 35\text{ A}$	20	94		S
Drain Leakage Current	I_{DSS}	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			10	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			±10	μA
Input Capacitance	C_{iss}	$V_{DS} = 10\text{ V}$		7200	10900	pF
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$		2000	3000	pF
Reverse Transfer Capacitance	C_{riss}	$f = 1\text{ MHz}$		700	1300	pF
Turn-on Delay Time	$t_{d(on)}$	$I_D = 35\text{ A}$		50	110	ns
Rise Time	t_r	$V_{GS(on)} = 10\text{ V}$		650	1700	ns
Turn-off Delay Time	$T_{d(off)}$	$V_{DD} = 30\text{ V}$		450	900	ns
Fall Time	t_f	$R_G = 10\ \Omega$		800	2000	ns
Total Gate Charge	Q_G	$I_D = 70\text{ A}$		150	230	nC
Gate to Source Charge	Q_{GS}	$V_{DD} = 48\text{ V}$		19		nC
Gate to Drain Charge	Q_{GD}	$V_{GS} = 10\text{ V}$		40		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	$I_F = 70\text{ A}, V_{GS} = 0\text{ V}$		0.97		V
Reverse Recovery Time	t_{rr}	$I_F = 70\text{ A}, V_{GS} = 0\text{ V}$		80		ns
Reverse Recovery Charge	Q_{rr}	$di/dt = 100\text{ A}/\mu\text{s}$		256		nC

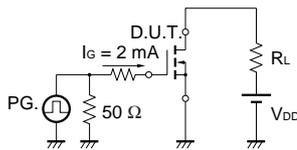
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE



TYPICAL CHARACTERISTICS (T_A = 25°C)

Figure1. DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

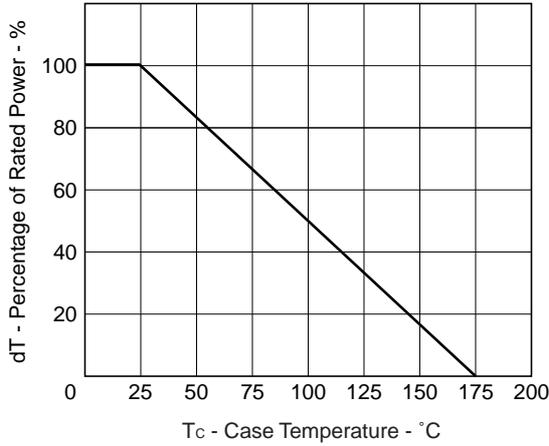


Figure2. TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

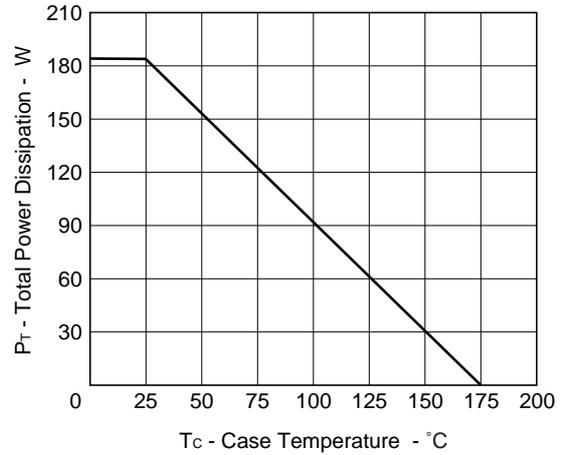


Figure3. FORWARD BIAS SAFE OPERATING AREA

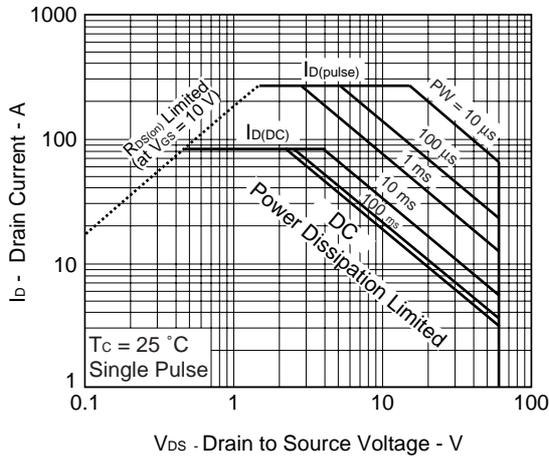


Figure4. SINGLE AVALANCHE ENERGY DERATING FACTOR

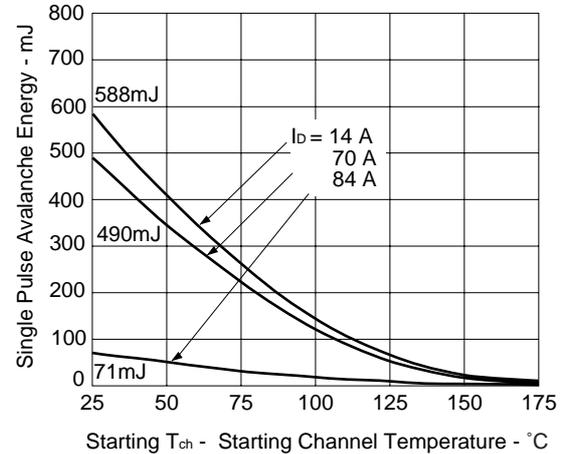


Figure5. FORWARD TRANSFER CHARACTERISTICS

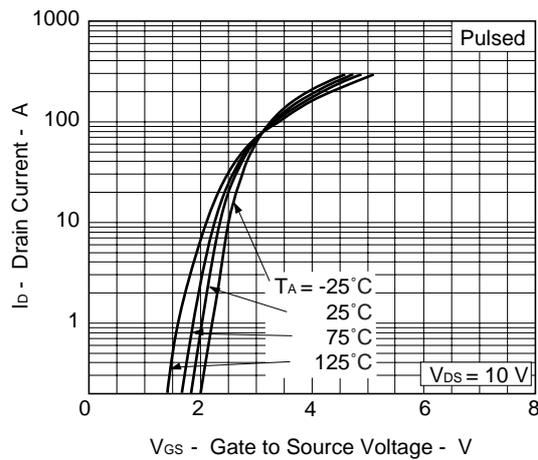


Figure6. DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

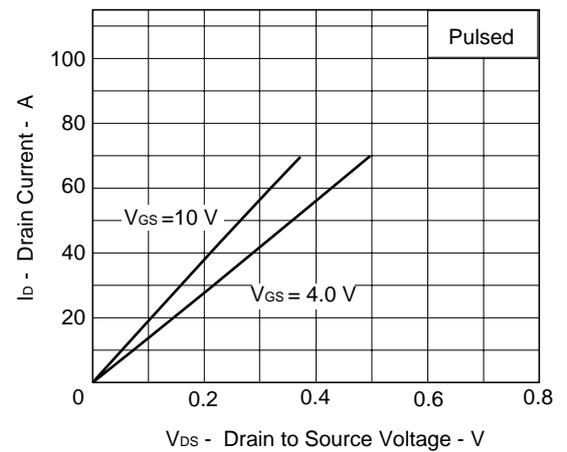


Figure7. TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

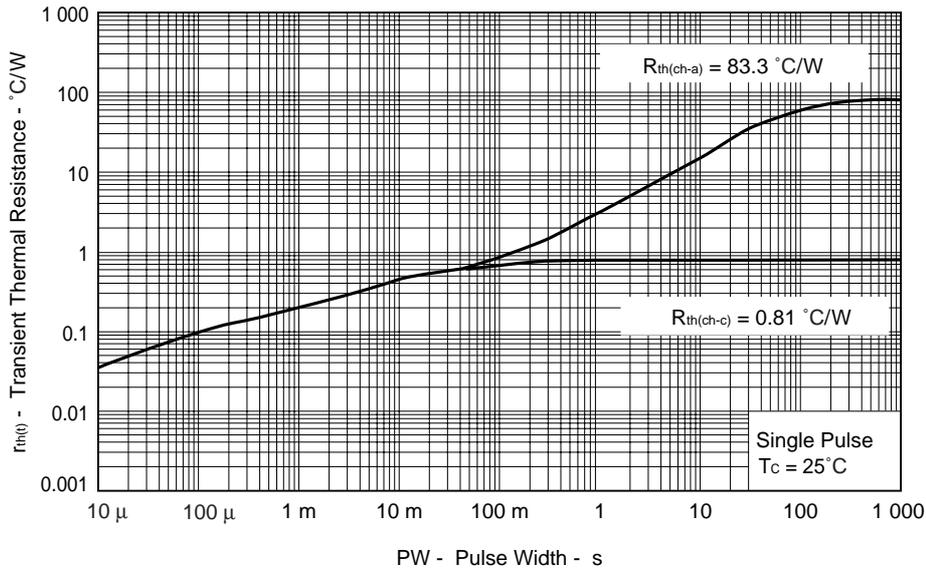


Figure8. FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

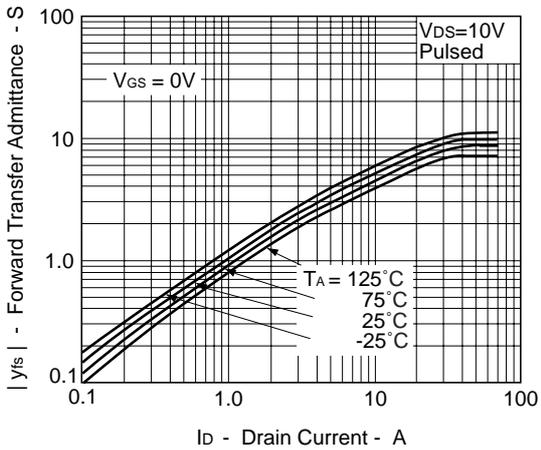


Figure9. DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

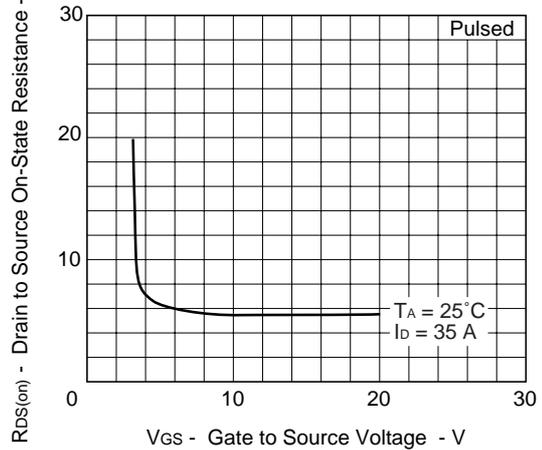


Figure10. DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

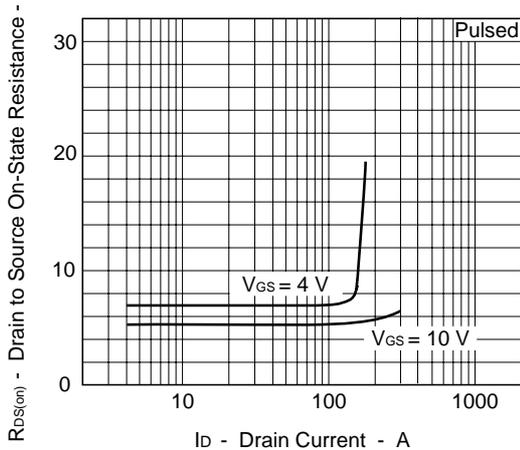


Figure11. GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

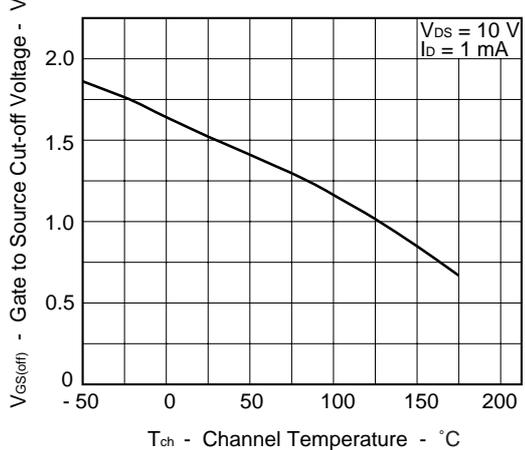


Figure12. DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

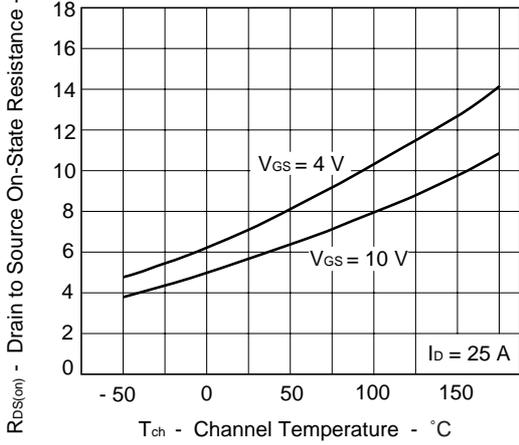


Figure13. SOURCE TO DRAIN DIODE FORWARD VOLTAGE

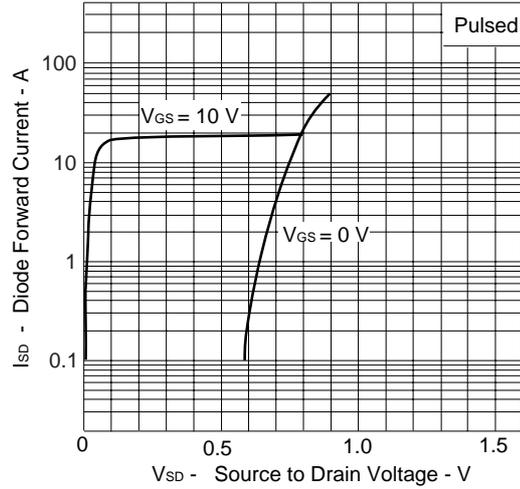


Figure14. CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

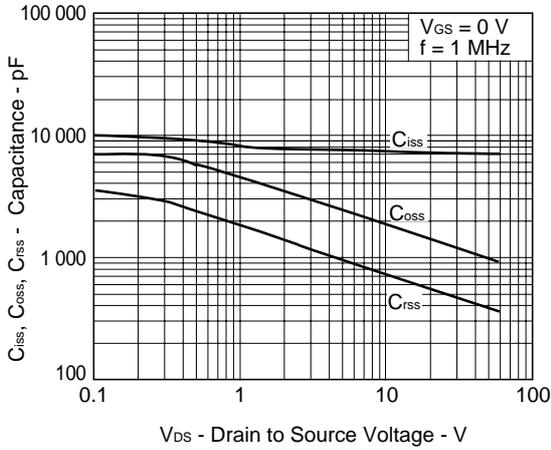


Figure15. SWITCHING CHARACTERISTICS

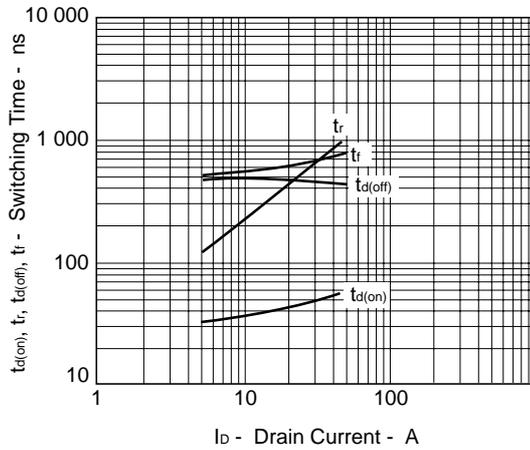


Figure16. REVERSE RECOVERY TIME vs. DRAIN CURRENT

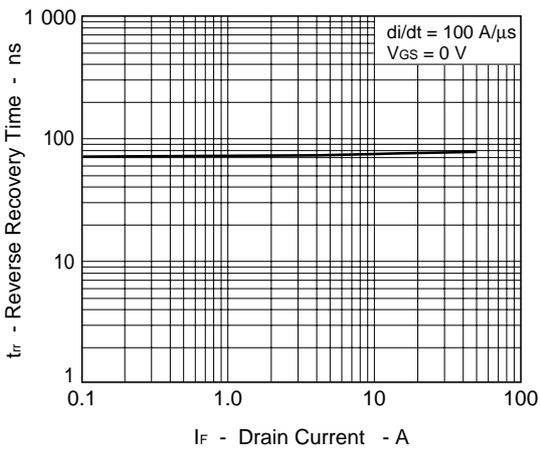
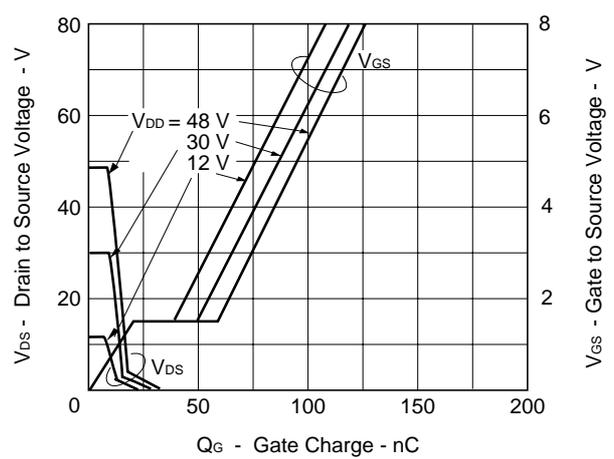
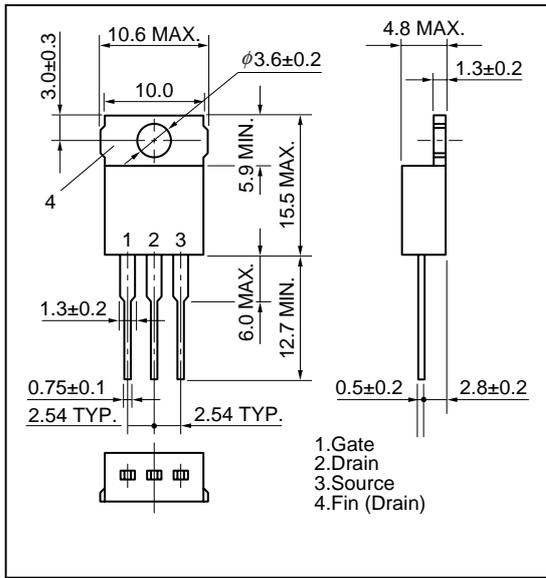


Figure17. DYNAMIC INPUT/OUTPUT CHARACTERISTICS

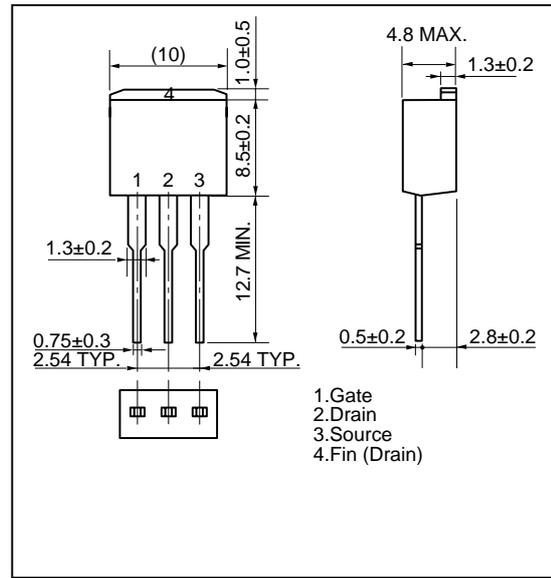


PACKAGE DRAWINGS (Unit : mm)

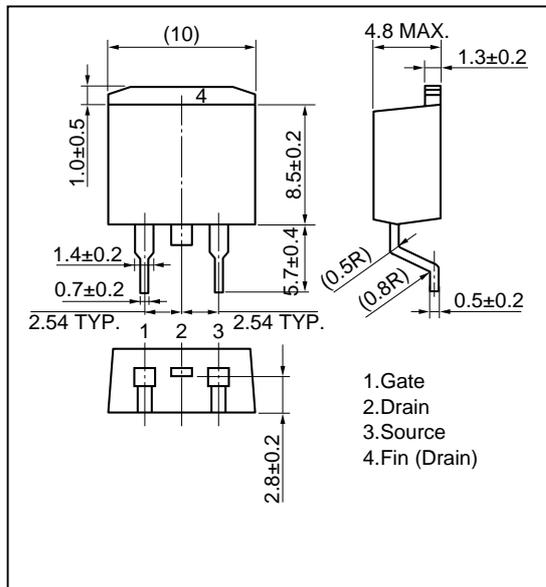
1)TO-220AB (MP-25)



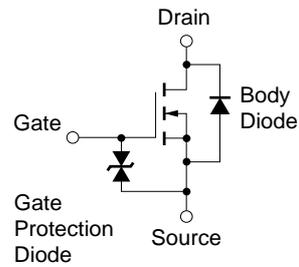
2)TO-262 (MP-25 Fin Cut)



3)TO-263 (JEDEC TYPE:MP-25ZJ)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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